

**Silicon PNP Power Transistors**

**2SB596**

**DESCRIPTION**

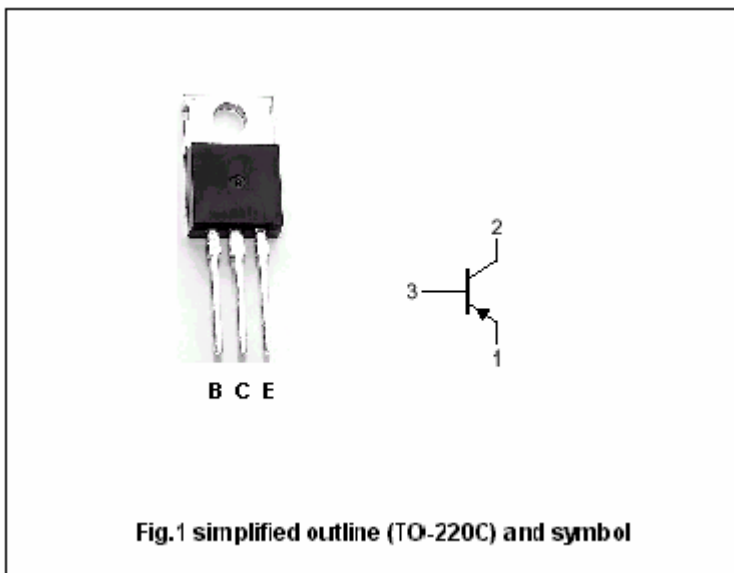
- With TO-220C package
- Complement to type 2SD526
- Good linearity of  $h_{FE}$

**APPLICATIONS**

- Power amplifier applications
- Recommend for 20 ~ 25W high fidelity audio frequency amplifier output stage

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute maximum ratings( $T_c=25$  )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-80	V
$V_{CEO}$	Collector-emitter voltage	Open base	-80	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-4	A
$I_E$	Emitter current		-4	A
$I_B$	Base current		-3	A
$P_C$	Collector power dissipation	$T_c=25$	30	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA; I <sub>B</sub> =0	-80			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-10mA; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3 A; I <sub>B</sub> =-0.3 A			-1.7	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-5V			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-80V; I <sub>E</sub> =0			-30	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-100	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-5V	40		240	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-5V	15			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-5V	3			MHz
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V; f=1MHz		130		pF

◆ h<sub>FE-1</sub> classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

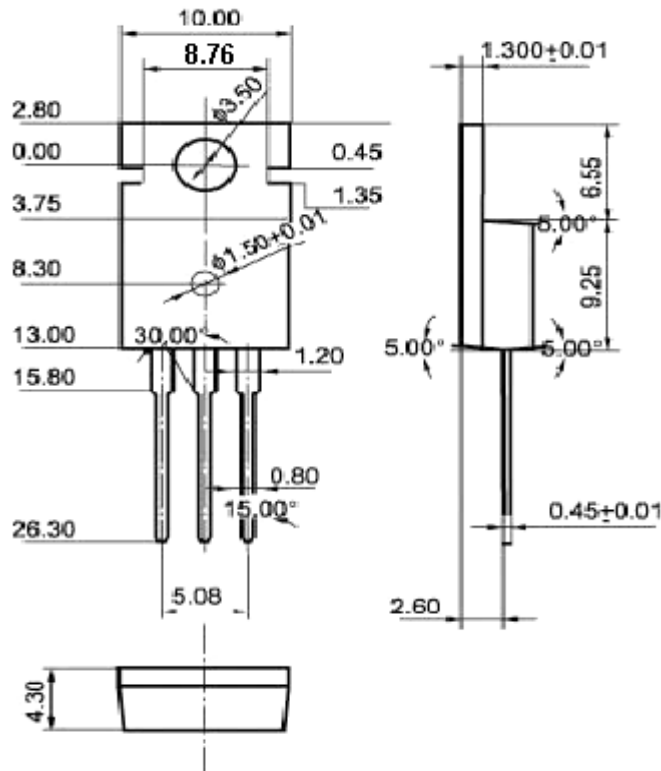


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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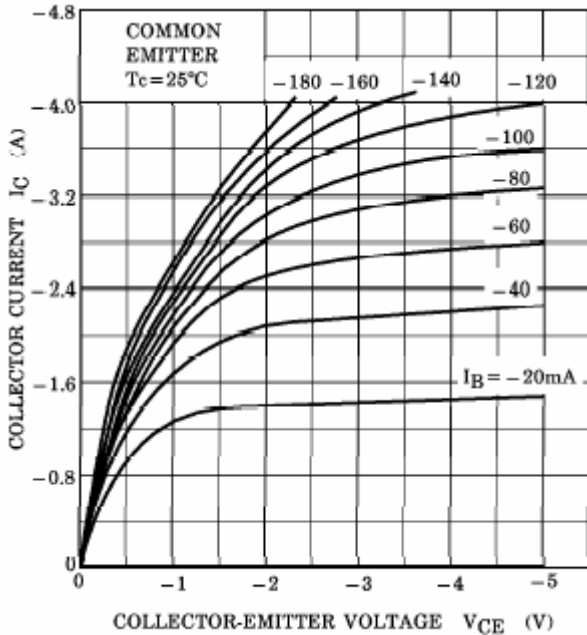


Fig.3 Static Characteristic

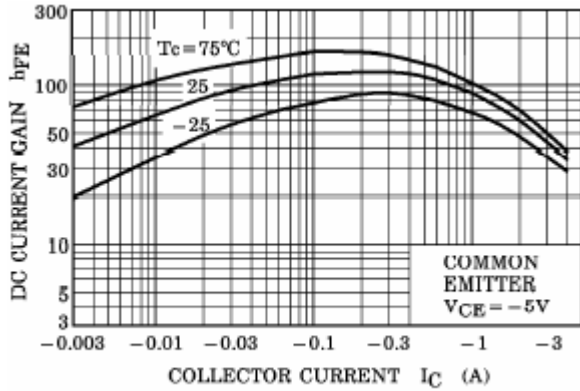


Fig.4 DC current Gain

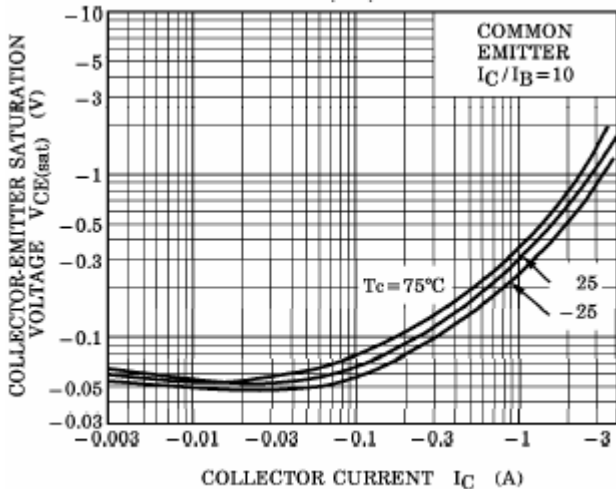


Fig.5 Collector-Emitter Saturation Voltage

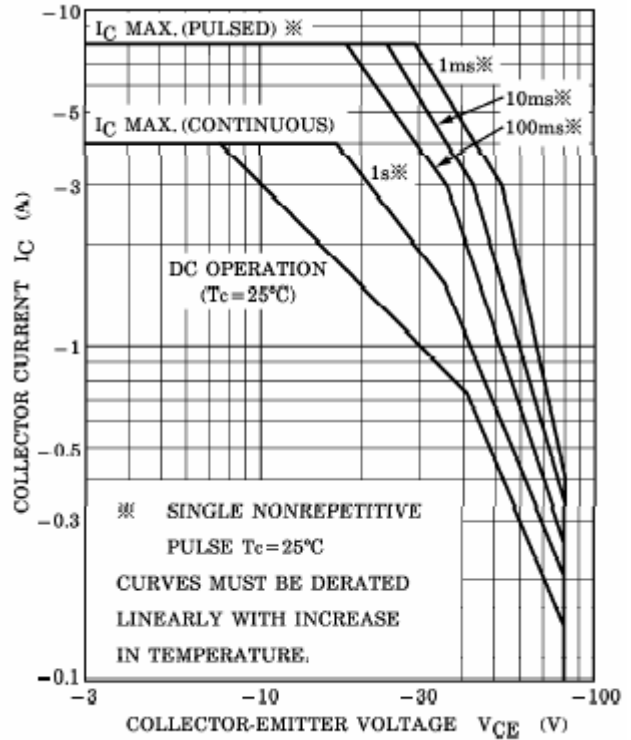


Fig.6 Safe Operating Area